

AMENDMENT TO THE SPECIFICATION

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Specifically, the structure shown in FIGS. 1A and 1B includes an effective memory cell region Rec where the memory capacitor MC, the storage node [NC] SN, the memory cell transistor TR and the like are formed, and the dummy cell region Rdc where the dummy lower electrode 33b, the capacitor insulating film extension 34b, the upper electrode extension 35b, the dummy cell plug 30b and the like are formed.

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Next, after depositing W/Ti multilayer film on the first interlayer insulating film 18, the W/Ti multiplayer film is patterned by the etching, so as to form a bit line 21a connected to the bit line plug 20b and a local interconnect 21b not connected to any other member but isolated at this stage. In patterning the W film, the etching end point of the W film is determined by detecting time when the surface of the Ti film is exposed, and in patterning the Ti film, the etching is performed under conditions for attaining high etching selectivity against [the first] a lower memory cell plug 20a of polysilicon.

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Thereafter, a BST ((BaSr)TiO₃) film with a thickness of approximately 30 nm, a Pt film with a thickness of approximately 30 nm, a TiAlN film with a thickness of approximately 6 nm and an NSG film are successively deposited so as to cover the second interlayer insulating film 22 and the lower electrode 33a. After patterning the NSG film into a hard mask 38, the TiAlN

film, the Pt film and the BST film are successively patterned by the dry etching using the hard mask 38, so as to form an upper barrier metal 36 covering the effective memory cell region Rec and the dummy cell region Rdc, a Pat film 35 including an upper electrode 35a and an upper electrode extension 35b and a BST film 34 including a capacitor insulating film 34a and a capacitor insulating film extension 34b. At this point, although the upper barrier metal 36, the upper electrode 35a and the upper electrode extension [34b] 35b are patterned so as to substantially completely cover the dummy cell plug 30b in Embodiment 1, they are patterned so as to expose at least a part of the dummy cell plug 30b in this embodiment. Thereafter, the hard mask 38 is selectively removed by using, for example, a diluted hydrofluoric acid solution.